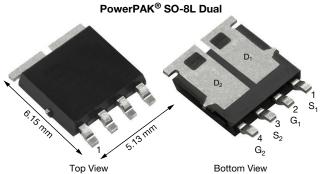
SQJ500AEP



Vishay Siliconix

Automotive N- and P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	1	
	N-CHANNEL	P-CHANNEL
V _{DS} (V)	40	-40
$R_{DS(on)} (\Omega)$ at $V_{GS} = \pm 10 \text{ V}$	0.0092	0.0270
$R_{DS(on)} (\Omega)$ at $V_{GS} = \pm 4.5 \text{ V}$	0.0112	0.0435
I _D (A)	30	-30
Configuration	N- and	P-Pair

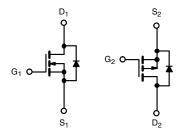


FEATURES

- TrenchFET[®] Power MOSFET
- AEC-Q101 Qualified^d
- 100 % R_a and UIS Tested
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE



N-Channel MOSFET P-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ500AEP-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T	_C = 25 °C, unless	otherwise n	oted)			
PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT		
Drain-Source Voltage		V _{DS}	40	-40	v	
Gate-Source Voltage		V _{GS}	±	20	v	
Continuous Drain Current ^a	T _C = 25 °C	I.,	30	-30		
	T _C = 125 °C	ID	30	-18		
Continuous Source Current (Diode Conduction) ^a		I _S	30	-30	А	
Pulsed Drain Current ^b		I _{DM}	120	-120	1	
Single Pulse Avalanche Current	L _ 0.1 mH	I _{AS}	26.5	-25		
Single Pulse Avalanche Energy L = 0.1 mH		E _{AS}	35	31	mJ	
Maximum Dawar Disaination ^b	T _C = 25 °C	Р	48	48	W	
Maximum Power Dissipation ^b	T _C = 125 °C	PD	16	16		
Operating Junction and Storage Temperature Ran	nge	T _J , T _{stg}	-55 to +175		℃	
Soldering Recommendations (Peak Temperature)	e, f		2	60		

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	85	85	°C/W
Junction-to-Case (Drain)		R _{thJC}	3.1	3.1	0/10

Notes

a. Package limited.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

c. When mounted on 1" square PCB (FR4 material).

d. Parametric verification ongoing.

f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

S13-2581-Rev. A, 23-Dec-13

1

Document Number: 62878

For technical questions, contact: automostechsupport@vishay.com

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e. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

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SHAY

SQJ500AEP	

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PARAMETER	SYMBOL		TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					1	•	1		
	Ň	V _{GS} =	= 0 V, I _D = 250 μΑ	N-Ch	40	-	-		
Drain-Source Breakdown Voltage	Source Breakdown Voltage V_{DS} $V_{GS} = 0 V, I_D = -250 \mu A$		0 V, I _D = - 250 μA	P-Ch	-40	-	-		
	M	V _{DS} =	: V _{GS} , I _D = 250 μΑ	N-Ch	1.3	1.8	2.3	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = - 250 μΑ	P-Ch	-1.5	-2	-2.5		
Onto Dourse Looke as			0.1/. 1/. 00.1/	N-Ch	-	-	± 100	<u> </u>	
Gate-Source Leakage	I _{GSS}	v _{DS} =	0 V, V_{GS} = ± 20 V	P-Ch	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 40 V	N-Ch	-	-	1		
		$V_{GS} = 0 V$	V _{DS} = -40 V	P-Ch	-	-	-1		
Zaus Osta Valtana Dusia Ouwant		$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 125 °C	N-Ch	-	-	50		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -40 V, T _J = 125 °C	P-Ch	-	-	-50	μA	
		$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 175 °C	N-Ch	-	-	150		
		$V_{GS} = 0 V$	V _{DS} = -40 V, T _J = 175 °C	P-Ch	-	-	-150		
		V _{GS} = 10 V	$V_{DS} \ge 5 V$	N-Ch	25	-	-		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le 5 V$	P-Ch	-25	-	-	A	
		V _{GS} = 10 V	I _D = 9.8 A	N-Ch	-	0.0077	0.0092		
		V _{GS} = -10 V	I _D = -6 A	P-Ch	-	0.0220	0.0270		
	R _{DS(on)}	V _{GS} = 10 V	I _D = 9.8 A, T _J = 125 °C	N-Ch	-	-	0.0138	Ω	
		V _{GS} = -10 V	I _D = -6 A, T _J = 125 °C	P-Ch	-	-	0.0380		
Drain-Source On-State Resistance ^a		V _{GS} = 10 V	I _D = 9.8 A, T _J = 175 °C	N-Ch	-	-	0.0170		
		V _{GS} = -10 V	I _D = -6 A, T _J = 175 °C	P-Ch	-	-	0.0460		
		V _{GS} = 4.5 V	I _D = 8.9 A	N-Ch	-	0.0094	0.0112		
		V _{GS} = -4.5 V	I _D = -4.7 A	P-Ch	-	0.0360	0.0435	1	
			= 15 V, I _D = 9.8 A	N-Ch	-	65	-	_	
Forward Transconductance ^b	9 _{fs}	V _{DS} :	= -15 V, I _D = -6 A	P-Ch	-	16	-	S	
Dynamic ^b		•				•			
	_	$V_{GS} = 0 V$	V _{DS} = 20 V, f = 1 MHz	N-Ch	-	1474	1843		
Input Capacitance	C _{iss}	$V_{GS} = 0 V$	V _{DS} = -20 V, f = 1 MHz	P-Ch	-	1302	1628		
	<u> </u>	$V_{GS} = 0 V$	V _{DS} = 20 V, f = 1 MHz	N-Ch	-	218	273	_	
Output Capacitance	Coss	$V_{GS} = 0 V$	V _{DS} = -20 V, f = 1 MHz	P-Ch	-	222	278	pF	
	0	$V_{GS} = 0 V$	V _{DS} = 20 V, f = 1 MHz	N-Ch	-	89	111		
Reverse Transfer Capacitance	C _{rss}	$V_{GS} = 0 V$	V _{DS} = -20 V, f = 1 MHz	P-Ch	-	154	193		
T + 1 O + O + O	_	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 10 A	N-Ch	-	25.5	38.3	+	
Total Gate Charge ^c	Qg	V _{GS} = -10 V	V _{DS} = -20 V, I _D = -10 A	P-Ch	-	30.2	45	1	
	_	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 10 A	N-Ch	-	4.4	-	nC	
Gate-Source Charge ^c	Q_gs	V _{GS} = -10 V	V _{DS} = -20 V, I _D = -10 A	P-Ch	-	4.1	-	1	
		V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	N-Ch	-	4.3	-	1	
Gate-Drain Charge ^c	Q _{gd}	V _{GS} = -10 V	V _{DS} = -20 V, I _D = -10 A	P-Ch	-	7.4	-	1	
	_			N-Ch	0.65	1.37	2.1	_	
Gate Resistance	Rg		f = 1 MHz	P-Ch	3.1	6.15	9.5	Ω	



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SPECIFICATIONS (T _C = 25	°C, unless o	otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Turn-On Delay Time ^c	+	$\label{eq:VDD} \begin{array}{l} V_{DD} = 20 \; V, \; R_{L} = 2 \; \Omega \\ I_{D} \cong 10 \; A, \; V_{GEN} = 10 \; V, \; R_{g} = 1 \; \Omega \end{array}$	N-Ch	-	8	12	
Tum-On Delay Time-	t _{d(on)}	$V_{\text{DD}} = -20 \text{ V}, \text{ R}_{\text{L}} = 2 \Omega$ $\text{I}_{\text{D}} \cong -10 \text{ A}, \text{ V}_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	P-Ch	-	7	11	
Rise Time ^c	+	$\label{eq:VDD} \begin{array}{l} V_{DD} = 20 \; V, \; R_L = 2 \; \Omega \\ I_D \cong 10 \; A, \; V_{GEN} = 10 \; V, \; R_g = 1 \; \Omega \end{array}$	N-Ch	-	12	18	
	t _r	$\label{eq:VDD} \begin{array}{l} V_{DD} = \text{-20 V, } R_L = 2 \ \Omega \\ I_D \cong \text{-10 A, } V_GEN = \text{-10 V, } R_g = 1 \ \Omega \end{array}$	P-Ch	-	9	13	
	+	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = \text{20 V}, \ R_{\text{L}} = \text{2} \ \Omega \\ I_{\text{D}} \cong \text{10 A}, \ V_{\text{GEN}} = \text{10 V}, \ R_{\text{g}} = \text{1} \ \Omega \end{array}$	N-Ch	-	22	33	ns A
Turn-Off Delay Time ^c	t _{d(off)}	$V_{\text{DD}} = -20 \text{ V}, \text{ R}_{\text{L}} = 2 \Omega$ $\text{I}_{\text{D}} \cong -10 \text{ A}, \text{ V}_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	P-Ch	-	43	64	
Fall Time ^c		$\label{eq:VDD} \begin{array}{l} V_{DD} = 20 \; V, \; R_{L} = 2 \; \Omega \\ I_{D} \cong 10 \; A, \; V_{GEN} = 10 \; V, \; R_{g} = 1 \; \Omega \end{array}$	N-Ch	-	10	16	
	t _f	$V_{\text{DD}} = -20 \text{ V}, \text{ R}_{\text{L}} = 2 \Omega$ $\text{I}_{\text{D}} \cong -10 \text{ A}, \text{ V}_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	N-Ch - P-Ch - N-Ch - N-Ch - P-Ch - P-Ch - N-Ch - P-Ch - N-Ch - N-Ch - P-Ch - P-Ch - P-Ch - P-Ch - P-Ch - P-Ch - N-Ch -	19	28		
Source-Drain Diode Ratings and C	haracteristics	5 ^b					
Pulsed Current ^a	1		N-Ch	-	-	120	^
	I _{SM}		P-Ch	-	-	-120	A
Forward Voltage	Var	I _S = 6.5 A	N-Ch	-	0.79	1.2	v
Forward Voltage	V _{SD}	I _S = -3.4 A	P-Ch	-	-0.78	-1.2	V

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

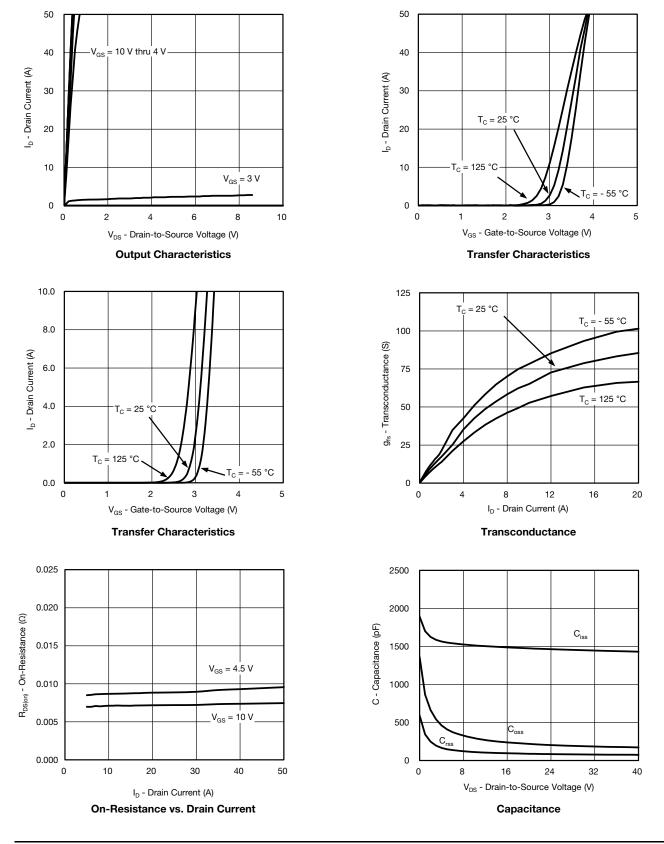
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

3



N-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



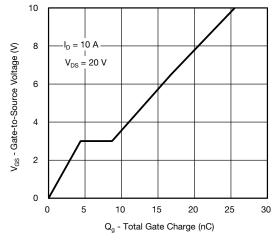
S13-2581-Rev. A, 23-Dec-13

4

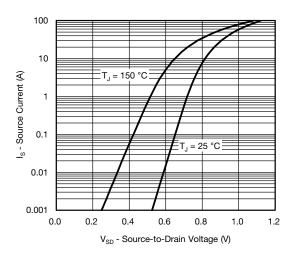
Document Number: 62878



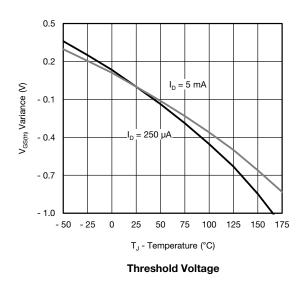
N-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

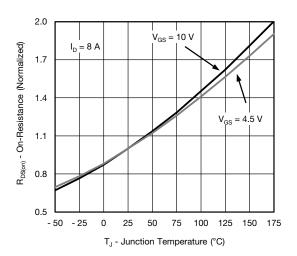




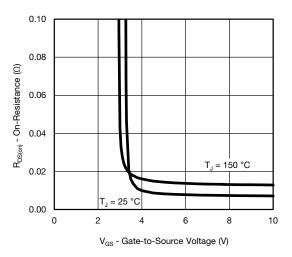


Source Drain Diode Forward Voltage

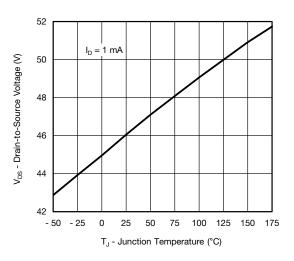




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

S13-2581-Rev. A, 23-Dec-13

5

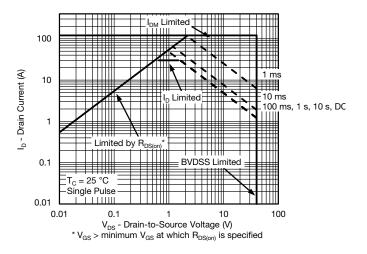
Document Number: 62878



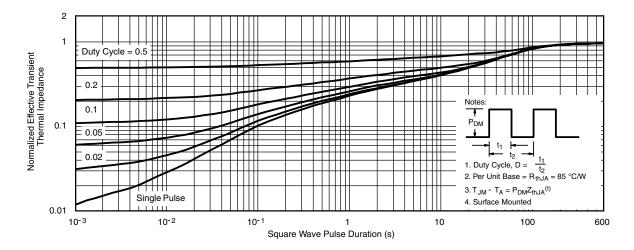
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N-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



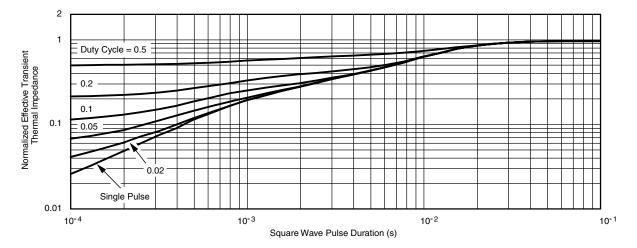
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



N-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

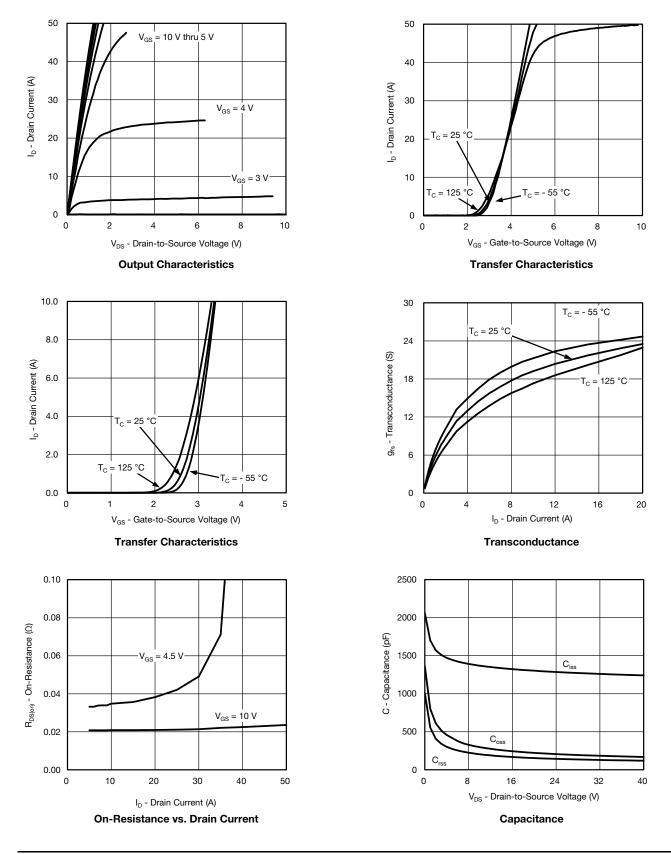
Note

- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



P-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

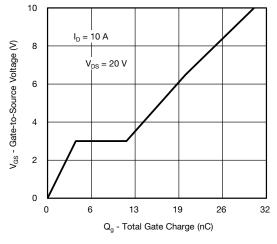


S13-2581-Rev. A, 23-Dec-13

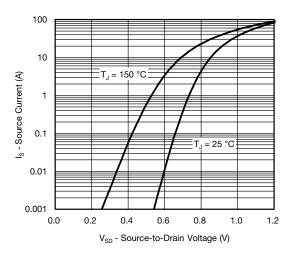
8 contact: automostech Document Number: 62878



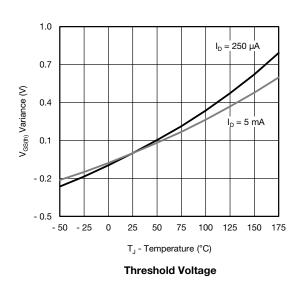
P-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

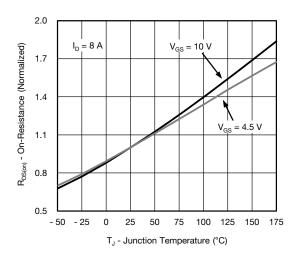




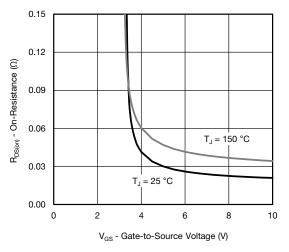


Source Drain Diode Forward Voltage

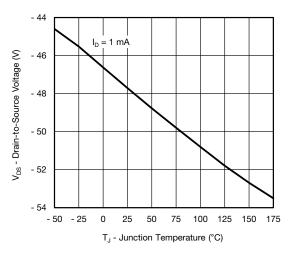




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

S13-2581-Rev. A, 23-Dec-13

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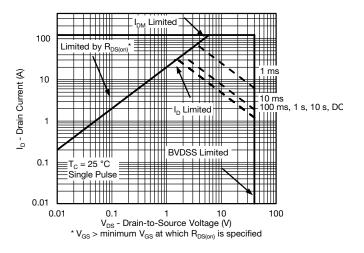
Document Number: 62878



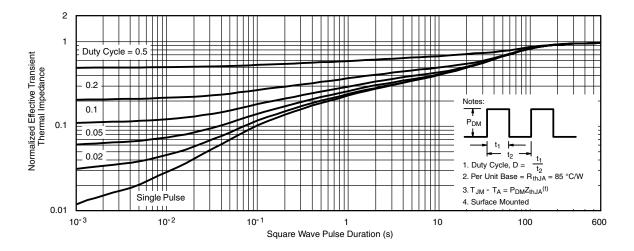
SQJ500AEP

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P-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



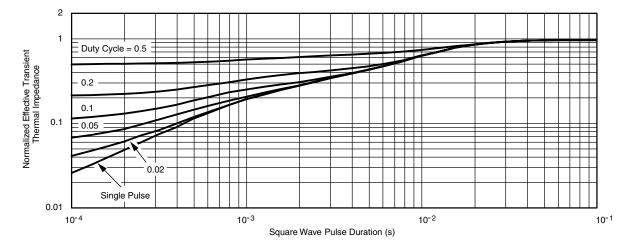
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



P-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg262878.



PowerPAK[®] SO-8L

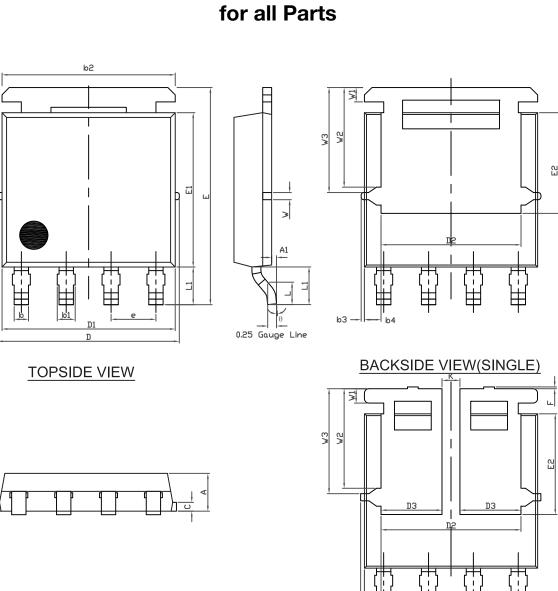
Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK SO-8L package:

DATASHEET PART NUMBER	OLD ORDERING CODE ^a	NEW ORDERING CODE
SQJ200EP	_	SQJ200EP-T1_GE3
SQJ202EP		SQJ202EP-T1_GE3
SQJ401EP	SQJ401EP-T1-GE3	SQJ401EP-T1_GE3
SQJ402EP	SQJ402EP-T1-GE3	SQJ402EP-T1_GE3
SQJ403EEP	SQJ403EEP-T1-GE3	SQJ403EEP-T1_GE3
SQJ403EP	-	SQJ403EP-T1_GE3
SQJ410EP	SQJ410EP-T1-GE3	SQJ410EP-T1_GE3
SQJ412EP	SQJ412EP-T1-GE3	SQJ412EP-T1_GE3
SQJ422EP	SQJ422EP-T1-GE3	SQJ422EP-T1_GE3
SQJ431EP	SQJ431EP-T1-GE3	SQJ431EP-T1_GE3
SQJ443EP	SQJ443EP-T1-GE3	SQJ443EP-T1_GE3
SQJ446EP	-	SQJ446EP-T1_GE3
SQJ456EP	SQJ456EP-T1-GE3	SQJ456EP-T1_GE3
SQJ459EP	-	SQJ459EP-T1_GE3
SQJ460AEP	-	SQJ460AEP-T1_GE3
SQJ461EP	SQJ461EP-T1-GE3	SQJ461EP-T1_GE3
SQJ463EP	SQJ463EP-T1-GE3	SQJ463EP-T1_GE3
SQJ465EP	SQJ465EP-T1-GE3	SQJ465EP-T1_GE3
SQJ469EP	SQJ469EP-T1-GE3	SQJ469EP-T1_GE3
SQJ486EP	SQJ486EP-T1-GE3	SQJ486EP-T1_GE3
SQJ488EP	SQJ488EP-T1-GE3	SQJ488EP-T1_GE3
SQJ500AEP	SQJ500AEP-T1-GE3	SQJ500AEP-T1_GE3
SQJ840EP	SQJ840EP-T1-GE3	SQJ840EP-T1_GE3
SQJ844AEP	SQJ844AEP-T1-GE3	SQJ844AEP-T1_GE3
SQJ850EP	SQJ850EP-T1-GE3	SQJ850EP-T1_GE3
SQJ858AEP	SQJ858AEP-T1-GE3	SQJ858AEP-T1_GE3
SQJ886EP	SQJ886EP-T1-GE3	SQJ886EP-T1_GE3
SQJ910AEP	SQJ910AEP-T1-GE3	SQJ910AEP-T1_GE3
SQJ912AEP	SQJ912AEP-T1-GE3	SQJ912AEP-T1_GE3
SQJ940EP	SQJ940EP-T1-GE3	SQJ940EP-T1_GE3
SQJ942EP	SQJ942EP-T1-GE3	SQJ942EP-T1_GE3
SQJ951EP	SQJ951EP-T1-GE3	SQJ951EP-T1_GE3
SQJ952EP	-	SQJ952EP-T1_GE3
SQJ956EP	SQJ956EP-T1-GE3	SQJ956EP-T1_GE3
SQJ960EP	SQJ960EP-T1-GE3	SQJ960EP-T1_GE3
SQJ963EP	SQJ963EP-T1-GE3	SQJ963EP-T1_GE3
SQJ968EP	SQJ968EP-T1-GE3	SQJ968EP-T1_GE3
SQJ980AEP	SQJ980AEP-T1-GE3	SQJ980AEP-T1_GE3
SQJ992EP	SQJ992EP-T1-GE3	SQJ992EP-T1_GE3

Note

a. Old ordering code is obsolete and no longer valid for new orders





PowerPAK[®] SO-8L Case Outline

Revision: 07-Sep-15

1

b3

BACKSIDE VIEW(DUAL)

Package Information



Vishay Siliconix

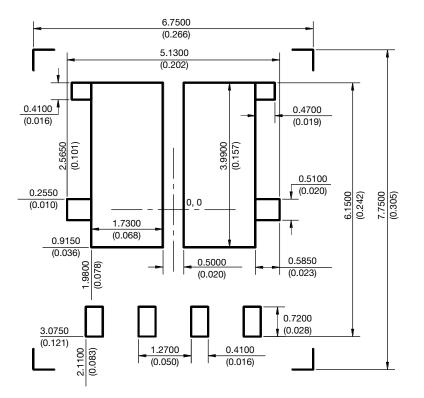
	MILLIMETERS				INCHES	
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX
А	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3		0.094	•		0.004	
b4		0.47			0.019	
С	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
е		1.27 BSC	•		0.050 BSC	
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	2.75	2.85	2.95	0.108	0.112	0.116
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
К		0.51	·		0.020	
W		0.23			0.009	
W1		0.41			0.016	
W2		2.82			0.111	
W3		2.96			0.117	
q	0°	-	10°	0°	-	10°

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)

Revision: 07-Feb-12



Vishay

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